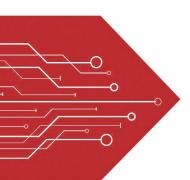
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FEATURES

- High Collector Current
- Complementary to PXT8050

SOT-89





3. EMITTER

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-40	V
V _{CEO}	Collector-Emitter Voltage	-25	V
V _{EBO}	Emitter-Base Voltage	-5	V
Ic	Collector Current -Continuous	-1.5	Α
Pc	Collector Power Dissipation	0.5	W
R _{ΘJA}	Thermal Resistance From Junction To Ambient	250 °C/W	
TJ	Junction Temperature	150 ℃	
T _{stg}	Storage Temperature	-55~150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

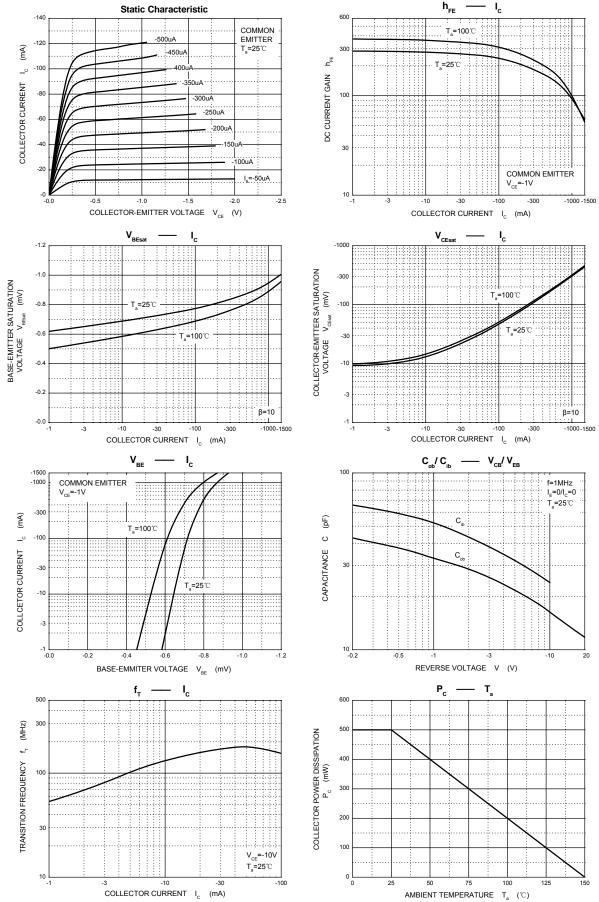
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	-40			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-25			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-40V, I _E =0			-100	nA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-100	nA
DC comment main	h _{FE(1)}	V _{CE} =-1V, I _C =-100mA	120		400	
DC current gain	h _{FE(2)}	V _{CE} =-1V, I _C =-800mA	40			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-800mA, I _B =-80mA			-0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-800mA, I _B =-80mA			-1.2	V
Base-emitter voltage	V_{BE}	V _{CE} =-1V, I _C =-10mA			-1	V
Transition frequency	f _T	V _{CE} =-10V,I _C =-50mA , f=30MHz	100			MHz
Collector output capacitance	Cob	V _{CB} =-10V, I _E =0, f=1MHz			20	pF

CLASSIFICATION OF h_{FE(1)}

RANK	L	Н	J
RANGE	120 - 200	200 - 350	300 - 400

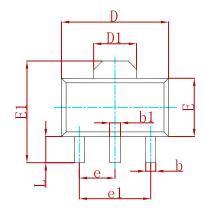


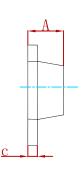
Typical Characteristics





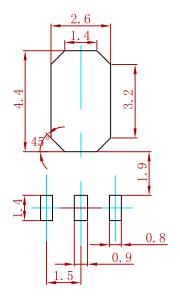
PACKAGE MECHANICAL DATA





Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	1.400	1.600	0.055	0.063	
b	0.320	0.520	0.013	0.020	
b1	0.400	0.580	0.016	0.023	
С	0.350	0.440	0.014	0.017	
D	4.400	4.600	0.173	0.181	
D1	1.550	REF.	0.061	REF.	
E	2.300	2.600	0.091	0.102	
E1	3.940	4.250	0.155	0.167	
е	1.500 TYP.		0.060 TYP.		
e1	3.000) TYP.	0.118	TYP.	
L	0.900	1.200	0.035	0.047	

Suggested Pad Layout



Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
PXT8550	SOT-89	1000





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